PBSS5250TH

50 V, 2 A PNP low VCEsat transistor

08 October 2024

Product data sheet

1. General description

PNP low V_{CEsat} transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- Higher efficiency leading to less heat genereation
- High temperature applications up to 175 °C

3. Applications

- Power management
- DC-to-DC conversion
- · Supply line switches
- Battery charger switches
- Peripheral drivers
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-50	V
I _C	collector current			-	-	-2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-3	А
R _{CEsat}	collector-emitter saturation resistance	$I_C = -2 \text{ A}; I_B = -200 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	150	mΩ

[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$



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5. Pinning information

Table 2. Pinning information

Symbol	Description	Simplified outline	Graphic symbol
В	base	3	
E	emitter		C
С	collector		В
) E
		1 L 2	sym132
	B E	B base E emitter	B base E emitter C collector

6. Ordering information

Table 3. Ordering information

Type number	Package							
	Name	Description	Version					
PBSS5250TH	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23					

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS5250TH	FH%

[1] % = placeholder for manufacturing site code

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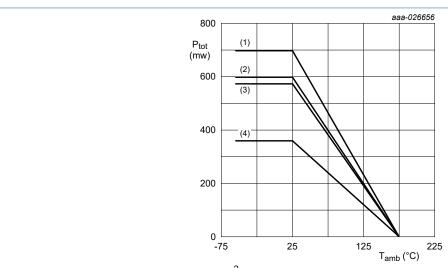
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-3	Α
I _B	base current			-	-300	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	360	mW
			[2]	-	575	mW
			[3]	-	600	mW
			[4]	-	700	mW
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

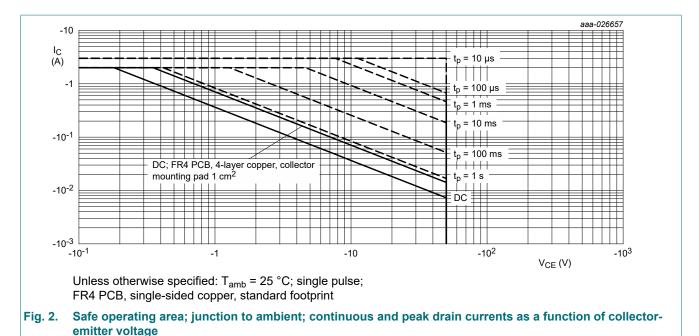
- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².



- (1) FR4 PCB, 4-layer copper, 1 cm²
- (2) FR4 PCB, 4-layer copper, standard footprint
- (3) FR4 PCB, single sided copper, 1 cm²
- (4) FR4 PCB, single sided copper, standard footprint

Fig. 1. Power derating curves for SOT23

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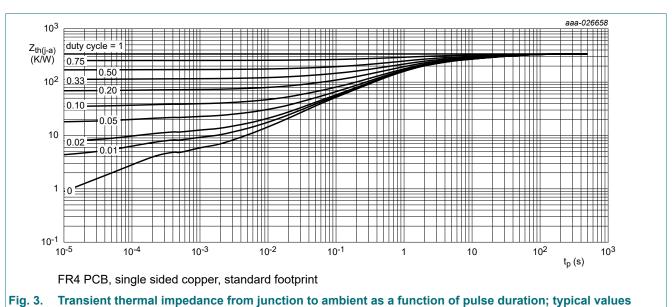


9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	417	K/W
	junction to ambient		[2]	-	-	261	K/W
			[3]	-	-	250	K/W
			[4]	-	-	215	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	75	-	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².



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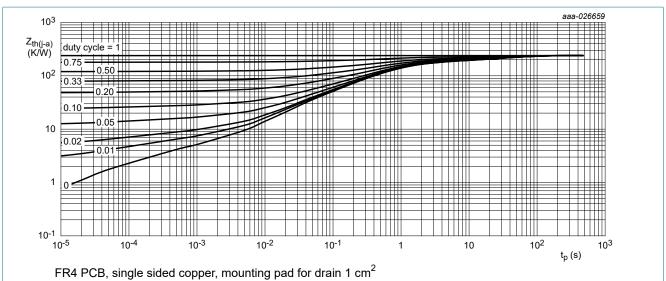
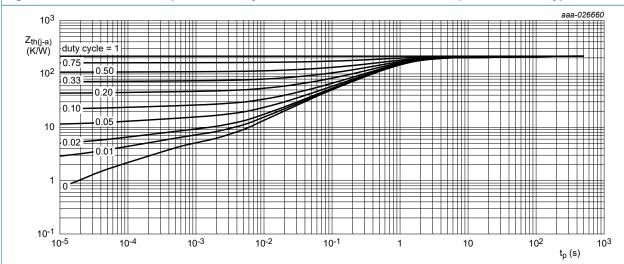
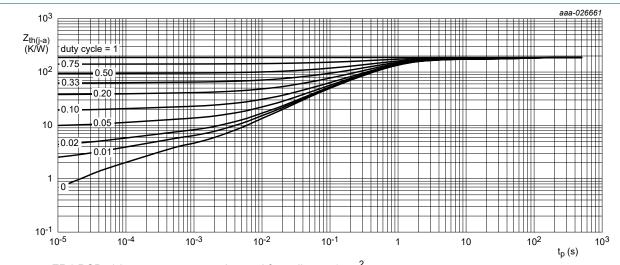


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, mounting pad for collector 1 cm²

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

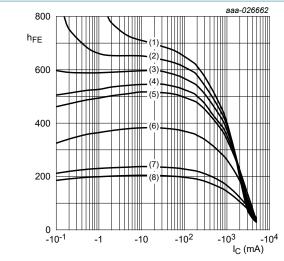
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		-50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-50	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_C = 0 \text{ mA}; I_E = -100 \mu\text{A}; T_{amb} = 25 \text{ °C}$		-7	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C		-	-	-100	nA
	current	V _{CB} = -50 V; I _E = 0 A; T _j = 150 °C		-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -100 mA; T_{amb} = 25 °C	[1]	200	-	-	
		V_{CE} = -2 V; I_{C} = -500 mA; T_{amb} = 25 °C	[1]	200	-	-	
		V _{CE} = -2 V; I _C = -1 A; T _{amb} = 25 °C	[1]	200	-	-	
		V_{CE} = -2 V; I_{C} = -2 A; T_{amb} = 25 °C	[1]	130	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -500 mA; I_B = -50 mA; T_{amb} = 25 °C	[1]	-	-	-90	mV
		I _C = -1 A; I _B = -50 mA; T _{amb} = 25 °C	[1]	-	-	-180	mV
		I _C = -2 A; I _B = -200 mA; T _{amb} = 25 °C	[1]	-	-	-300	mV
R _{CEsat}	collector-emitter saturation resistance		[1]	-	-	150	mΩ
V _{BEsat}	base-emitter saturation voltage	$I_C = -2 \text{ A}; I_B = -100 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	-1.1	V
V_{BE}	base-emitter voltage	V _{CE} = -2 V; I _C = -1 A	[1]	-	-	-1.2	V
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C		100	-	-	MHz
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	35	pF

^[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$

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 $V_{CE} = -2 V$

 $(1) T_{amb} = 175 °C$

(2) $T_{amb} = 150 \, ^{\circ}C$

(3) $T_{amb} = 125 \, ^{\circ}C$

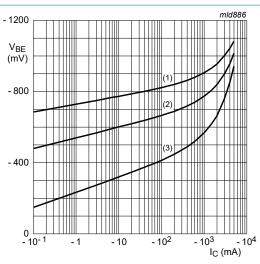
(4) $T_{amb} = 100 \, ^{\circ}C$

(5) T_{amb} = 85 °C

(6) $T_{amb} = 25 \, ^{\circ}C$ $(7) T_{amb} = -40 °C$

(8) $T_{amb} = -55 \, ^{\circ}C$

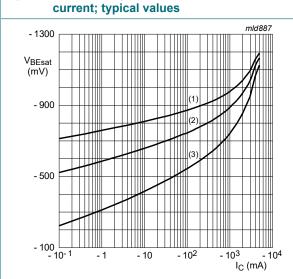
Fig. 7. DC current gain as a function of collector



 $V_{CE} = -2 V$ (1) $T_{amb} = -55 °C$ (2) $T_{amb} = 25 °C$

 $(3) T_{amb} = 150 °C$

Fig. 8. Base-emitter voltage as a function of collector current; typical values

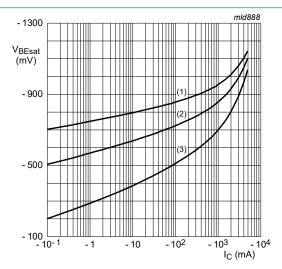


 $I_{\rm C}/I_{\rm B}=10$

(1) $T_{amb} = -55 \, ^{\circ}C$

(2) T_{amb} = 25 °C (3) T_{amb} = 150 °C





 $I_{\rm C}/I_{\rm B}=20$

(1) $T_{amb} = -55 \, ^{\circ}C$

(2) T_{amb} = 25 °C (3) T_{amb} = 150 °C

collector current; typical values

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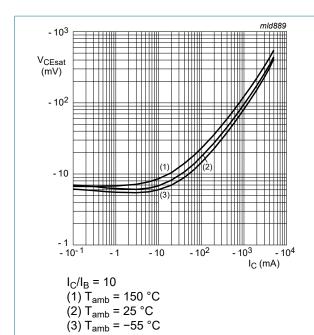


Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values

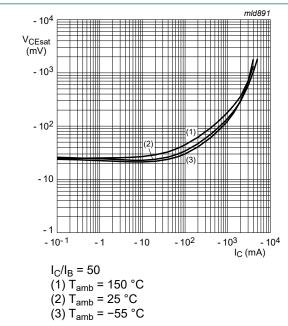
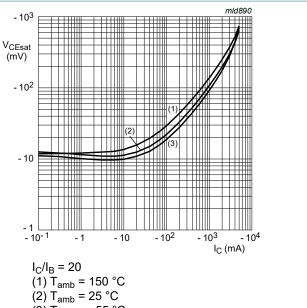
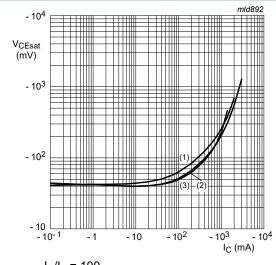


Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values



(1) $T_{amb} = 150 \text{ °C}$ (2) $T_{amb} = 25 \text{ °C}$ (3) $T_{amb} = -55 \text{ °C}$

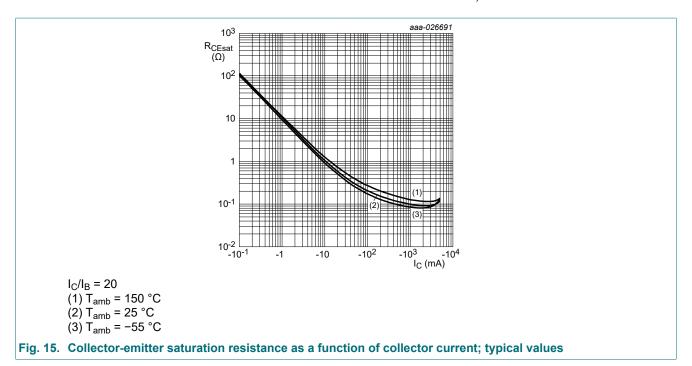
Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values



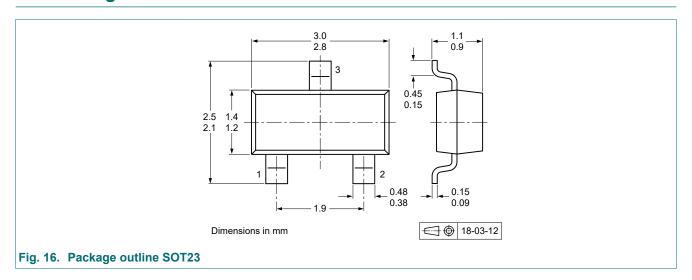
 $I_{\rm C}/I_{\rm B} = 100$ (1) $T_{amb} = 150 \, ^{\circ}C$ (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 14. Collector-emitter saturation voltage as a function of collector current; typical values

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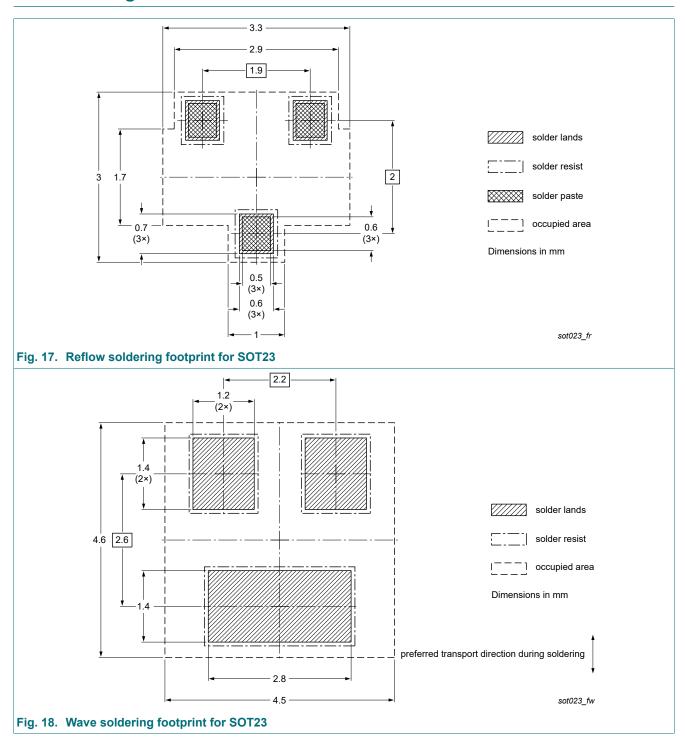


11. Package outline



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12. Soldering



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13. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBSS5250TH v.3	20241008	Product data sheet	-	PBSS5250TH v.2				
Modifications:	Product changed to	Product changed to non automotive. Please refer to the automotive product(s) with -Q.						
PBSS5250TH v.2	20170809	Product data sheet	-	PBSS5250TH v.1				
PBSS5250TH v.1	20170421	Product data sheet	-	-				

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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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